

Appl. No : 10/615,524
Filed : July 3, 2003

AMENDMENTS TO THE CLAIMS

The claims as listed below will replace all prior listings and presentations of claims in the above-identified application.

1. (CURRENTLY AMENDED) A method for forming a substantially haze-free BST film, comprising:

supplying BST sources into a chamber;

heating the chamber to a temperature above 600°C; and

depositing the BST film at a rate of between about 10 and about 100 Å/min while maintaining the chamber at a temperature above 600 °C, wherein the resulting BST film comprises about 52 to 53 atomic percent titanium.

2. (ORIGINAL) The method of Claim 1, wherein the BST film is deposited at a rate of less than about 80Å/min.

3. (PREVIOUSLY AMENDED) The method of Claim 1, wherein the chamber is heated to a temperature of up to about 680°C.

4. (ORIGINAL) The method of Claim 1, wherein the substrate is heated to a temperature of about 500 to 580 °C.

5. (ORIGINAL) The method of Claim 1, further comprising depositing an electrode material before depositing said BST film.

6. (ORIGINAL) The method of Claim 5, further comprising heating the substrate to a temperature of about 500 to 550 °C before depositing said electrode material.

7. (CANCELED)

8. (CANCELED)

9. (CURRENTLY AMENDED) A method for forming a substantially haze-free BST film, comprising: supplying BST sources into a chamber and depositing a BST film at a rate of between about 10 and about 100 Å/min, wherein the BST film is formed substantially uniformly with a (100) crystal orientation and wherein the resulting BST film comprises about 52 to 53 atomic percent titanium.

10. (CURRENTLY AMENDED) A method for forming a substantially haze-free BST film, comprising:

supplying BST sources into a chamber; and

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depositing a BST film at a chamber temperature above 600 °C and at a rate of between about 10 and about 100 Å/min until a BST film having a substantially uniform crystal orientation along planes in the {100} family and a thickness of about 150 to 300 Å is formed, wherein the resulting BST film comprises about 52 to 53 atomic percent titanium.

11. (ORIGINAL) The method of Claim 10, wherein the BST film is deposited at a rate of 80 Å/min.

12. (ORIGINAL) The method of Claim 10, further comprising forming a first electrode below the BST film, and forming a second electrode above the BST film.

13. (ORIGINAL) The method of Claim 10, further comprising heating the substrate to a temperature of about 500 to 550 °C before depositing said electrode material.

14. (CANCELED)

15. (CANCELED)